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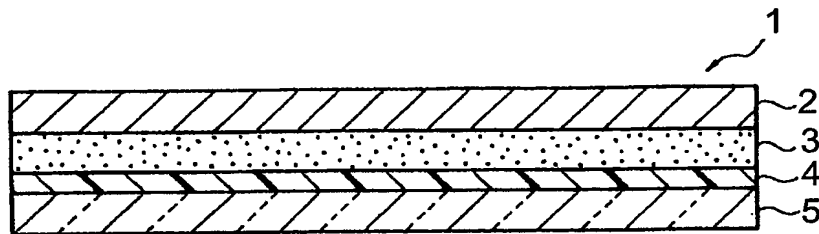
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- (71) Applicant (for all designated States except US): **3M INNOVATIVE PROPERTIES COMPANY** [US/US]; 3M Center, Post Office Box 33427, Saint Paul, MN 55133-3427 (US).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): **NODA, Kazuki** [JP/JP]; 8-8, Minami Hashimoto, 3-chome, Sagamihara, Kanagawa 229-1185 (JP). **IWASAWA, Masaru** [JP/JP]; 8-8, Minami Hashimoto, 3-chome, Sagamihara, Kanagawa 229-1185 (JP).
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(54) Title: PRODUCTION METHOD OF SEMICONDUCTOR CHIP



(57) Abstract: Provided is a method for producing a semiconductor chip, comprising applying a photothermal conversion layer on a light-transmitting support, provided that upon irradiation of radiation energy, the photothermal conversion layer converts the radiation energy into heat and decomposes due to the heat; laminating the semiconductor wafer and the light-transmitting support through a photocurable adhesive by placing the circuit face and the photothermal conversion layer to face each other, thereby forming a laminated body having a non-circuit face on the outside; grinding the non-circuit face of the semiconductor wafer until the semiconductor wafer reaches a desired thickness; dicing the ground semiconductor wafer from the non-circuit face side to cut it into a plurality of semiconductor chips; irradiating radiation energy from the light-transmitting support side to decompose the photothermal conversion layer, thereby causing separation into a semiconductor chips having the adhesive layer and a light-transmitting support; and optionally removing the adhesive layer from the semiconductor chips.

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